

Characterization of Rare Earth Doped III-V Thermoelectric Materials

Vishaal Varahamurthy

Ryan Need, B.S.

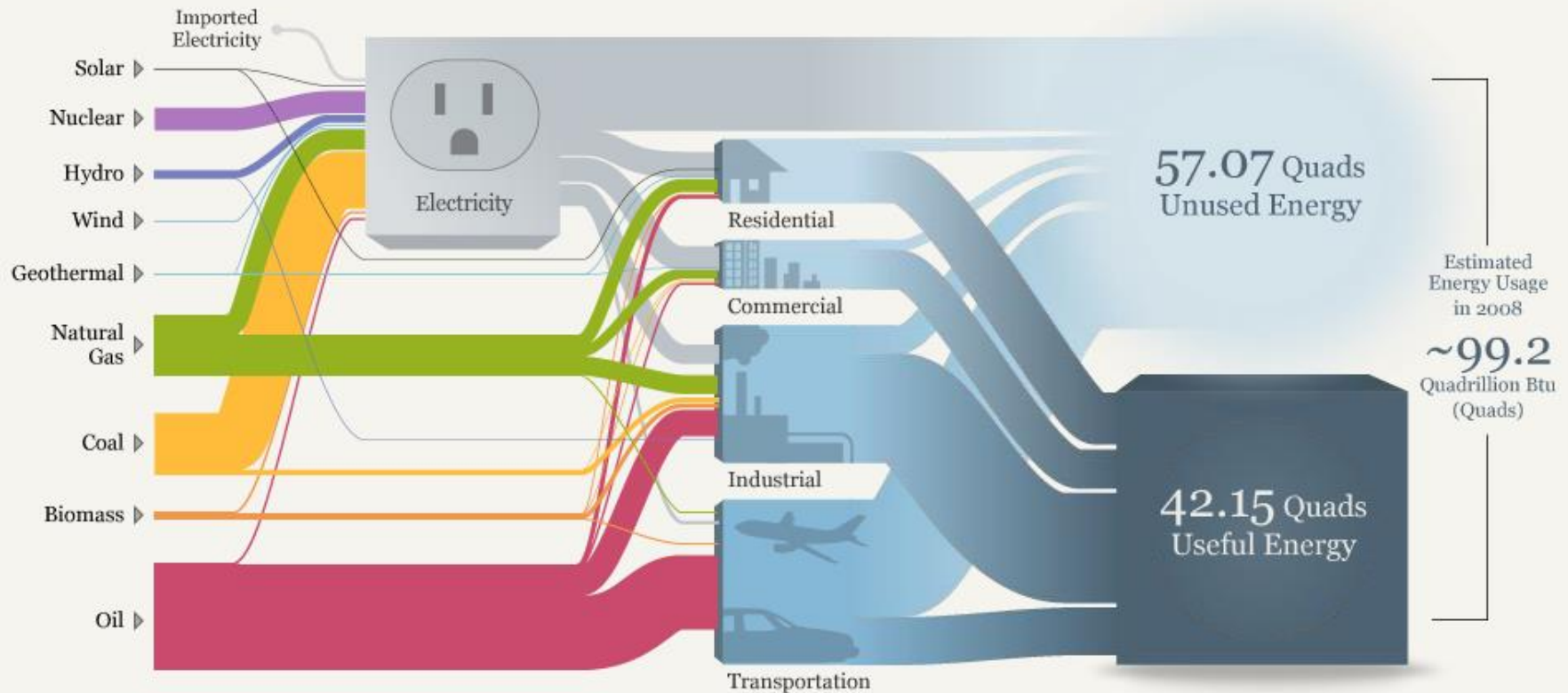
Christopher Palmstrøm, PhD

UCSB Materials Department

EUREKA

Energy: we lose more than we use

OUR ENERGY SYSTEM



What are Thermoelectrics?



Original image: www.themotorreview.com



Original image: nasa.gov

Convert waste heat into usable electricity

Solid-state, robust, and require little maintenance

The Thermoelectric Figure of Merit (ZT)

Seebeck Coefficient

Electrical Conductivity

$$ZT = \frac{\alpha^2 \sigma}{\kappa} T$$

Temperature

Thermal Conductivity

Maximizing Thermoelectric Performance

(HIGH)
Seebeck Coefficient

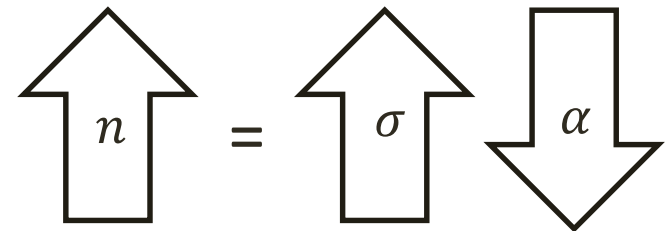
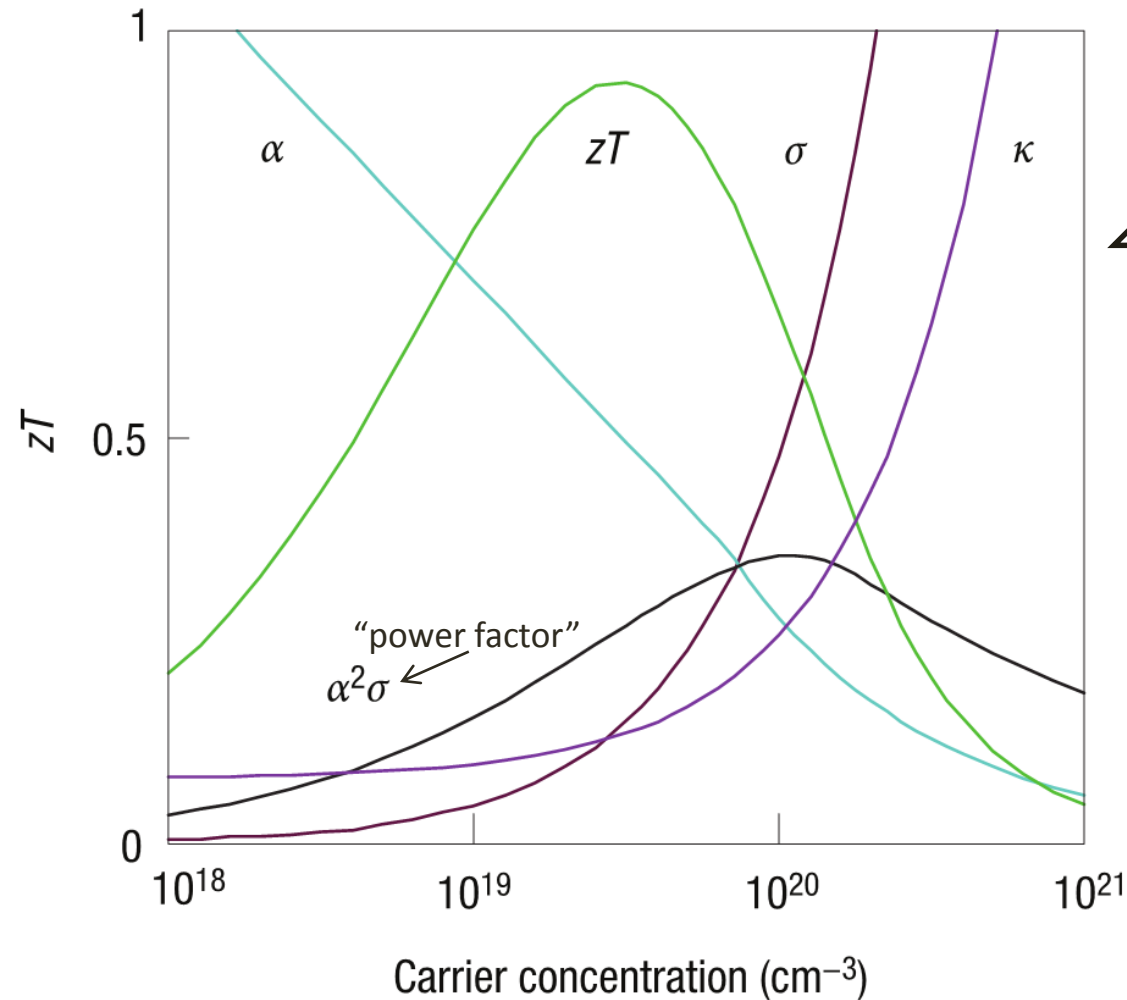
(HIGH)
Electrical Conductivity

$$ZT = \frac{\alpha^2 \sigma}{\kappa} T$$

← Temperature

↑
Thermal Conductivity
(LOW)

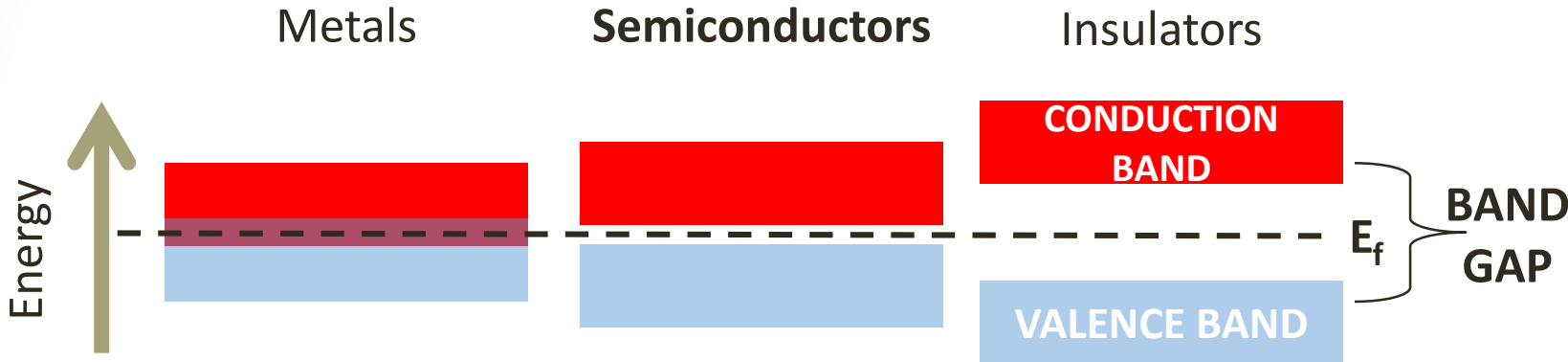
Balancing the Components of ZT



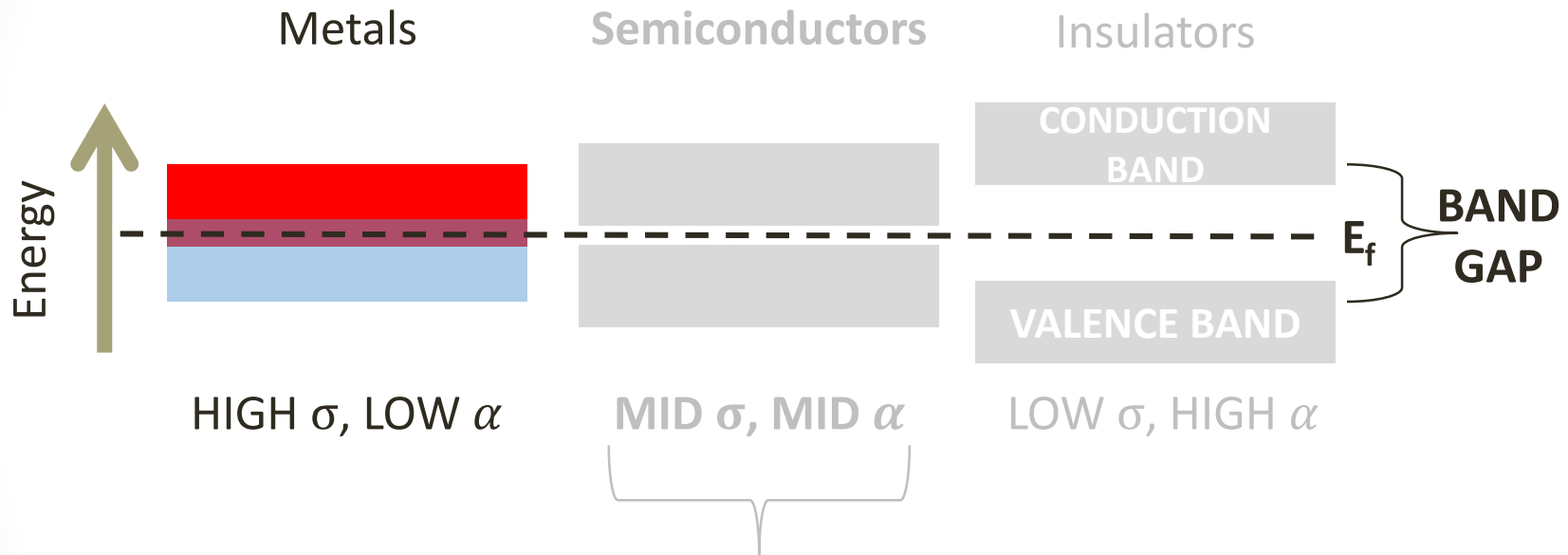
$$ZT = \frac{\alpha^2 \sigma}{\kappa} T$$

Red arrows indicate the direction of change for α (downward) and σ (upward) in the numerator.

Why Semiconductors?

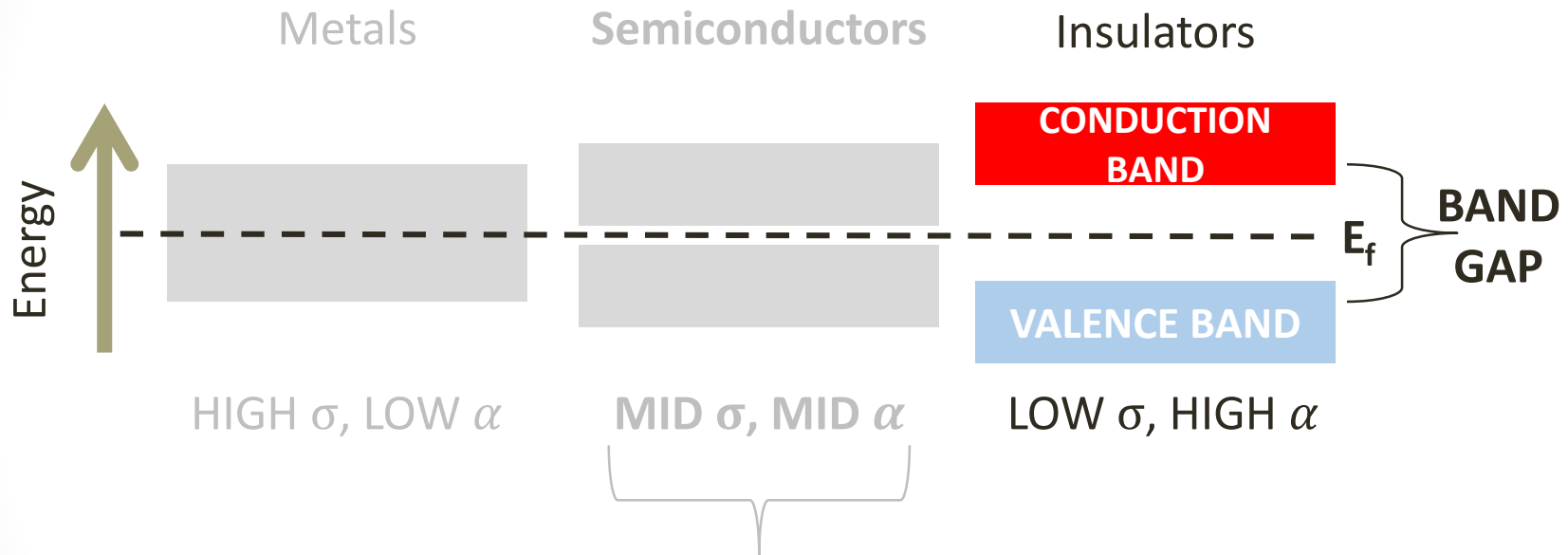


Why Semiconductors?



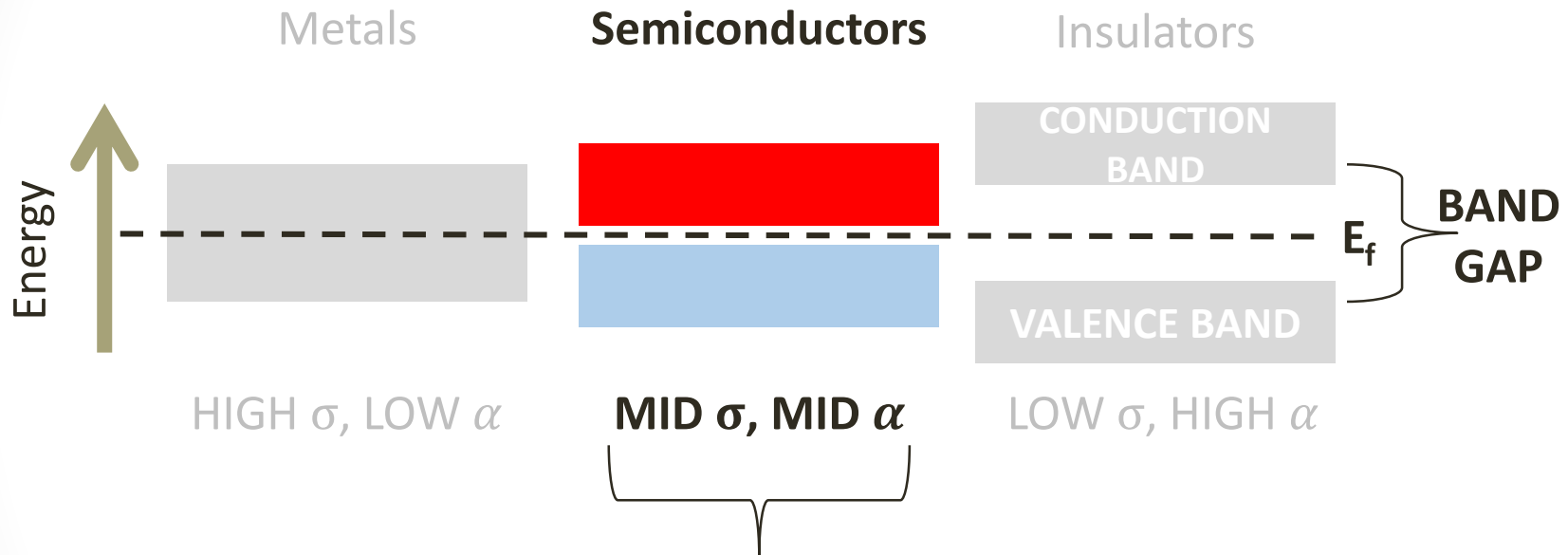
Can be tuned/optimized by adding impurities (doping)

Why Semiconductors?



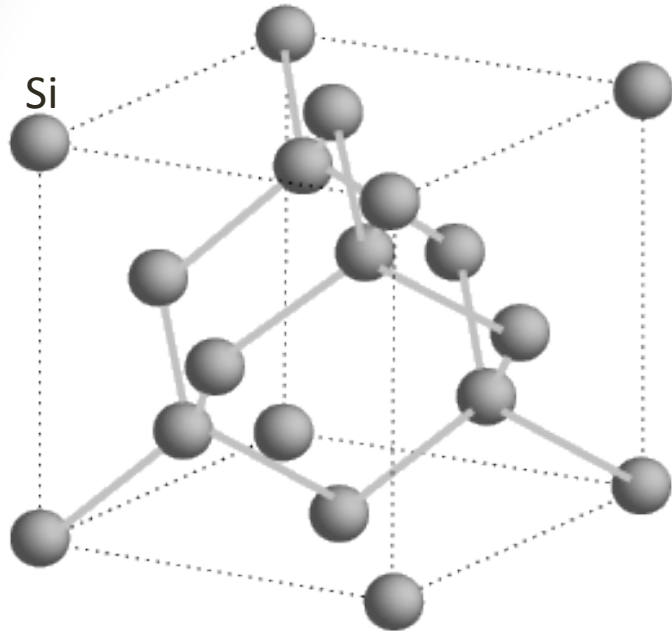
Can be tuned/optimized by adding impurities (doping)

Why Semiconductors?



Can be tuned/optimized by adding impurities (doping)

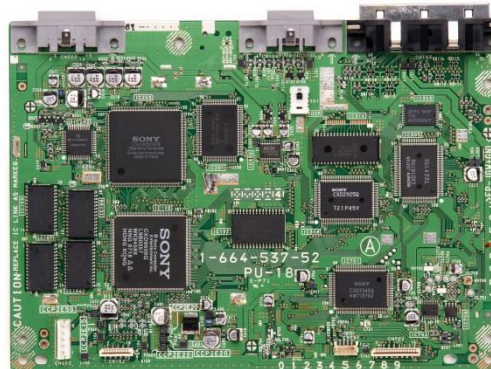
Conventional Semiconductors



Original image : <http://hyperphysics.phy-astr.gsu.edu/>

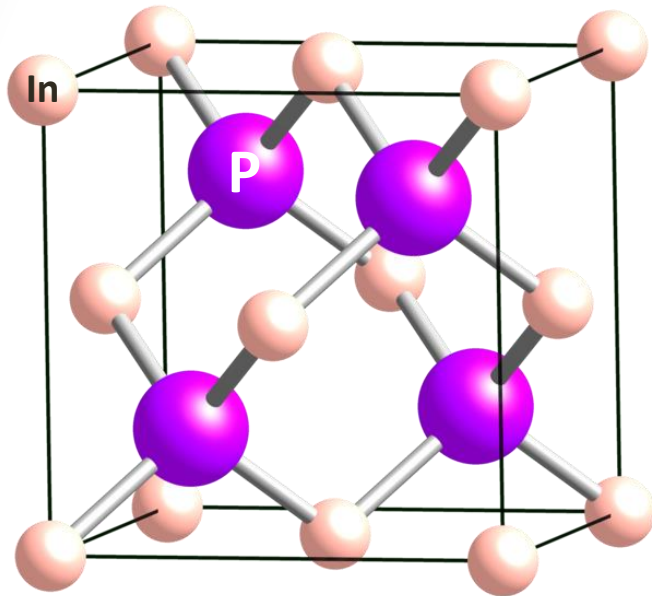
III	IV	V	VI
boron 5 B 10.811	carbon 6 C 12.011	nitrogen 7 N 14.007	oxygen 8 O 15.999
aluminium 13 Al 26.982	silicon 14 Si 28.086	phosphorus 15 P 30.974	sulfur 16 S 32.065
gallium 31 Ga 69.723	germanium 32 Ge 72.61	arsenic 33 As 74.922	selenium 34 Se 78.96
indium 49 In 114.82	tin 50 Sn 118.71	antimony 51 Sb 121.76	tellurium 52 Te 127.60
thallium 81 Tl 204.38	lead 82 Pb 207.2	bismuth 83 Bi 208.98	polonium 84 Po [209]

Original image: <http://www.bpc.edu/>



Original image : Wikimedia Commons

III-V Semiconductors



Original image: Public Domain

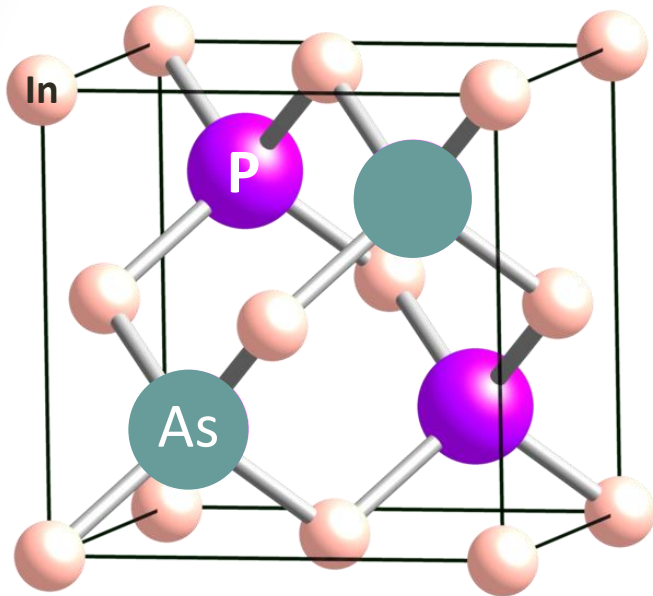
III	IV	V	VI
boron 5 B 10.811	carbon 6 C 12.011	nitrogen 7 N 14.007	oxygen 8 O 15.999
aluminium 13 Al 26.982	silicon 14 Si 28.086	phosphorus 15 P 30.974	sulfur 16 S 32.065
gallium 31 Ga 69.723	germanium 32 Ge 72.61	arsenic 33 As 74.922	selenium 34 Se 78.96
indium 49 In 114.82	tin 50 Sn 118.71	antimony 51 Sb 121.76	tellurium 52 Te 127.60
thallium 81 Tl 204.38	lead 82 Pb 207.2	bismuth 83 Bi 208.98	polonium 84 Po [209]

Original image: <http://www.bpc.edu/>

Can alloy elements from groups III and V to make III-V semiconductors

Different sizes of atoms causes a drop in thermal conductivity due to “phonon scattering”

Material System: $\text{InAs}_x\text{P}_{1-x}$



Original image: Public Domain

III	IV	V	VI
boron 5 B 10.811	carbon 6 C 12.011	nitrogen 7 N 14.007	oxygen 8 O 15.999
aluminium 13 Al 26.982	silicon 14 Si 28.086	phosphorus 15 P 30.974	sulfur 16 S 32.065
gallium 31 Ga 69.723	germanium 32 Ge 72.61	arsenic 33 As 74.922	selenium 34 Se 78.96
indium 49 In 114.82	tin 50 Sn 118.71	antimony 51 Sb 121.76	tellurium 52 Te 127.60
thallium 81 Tl 204.38	lead 82 Pb 207.2	bismuth 83 Bi 208.98	polonium 84 Po [209]

Original image: <http://www.bpc.edu/>

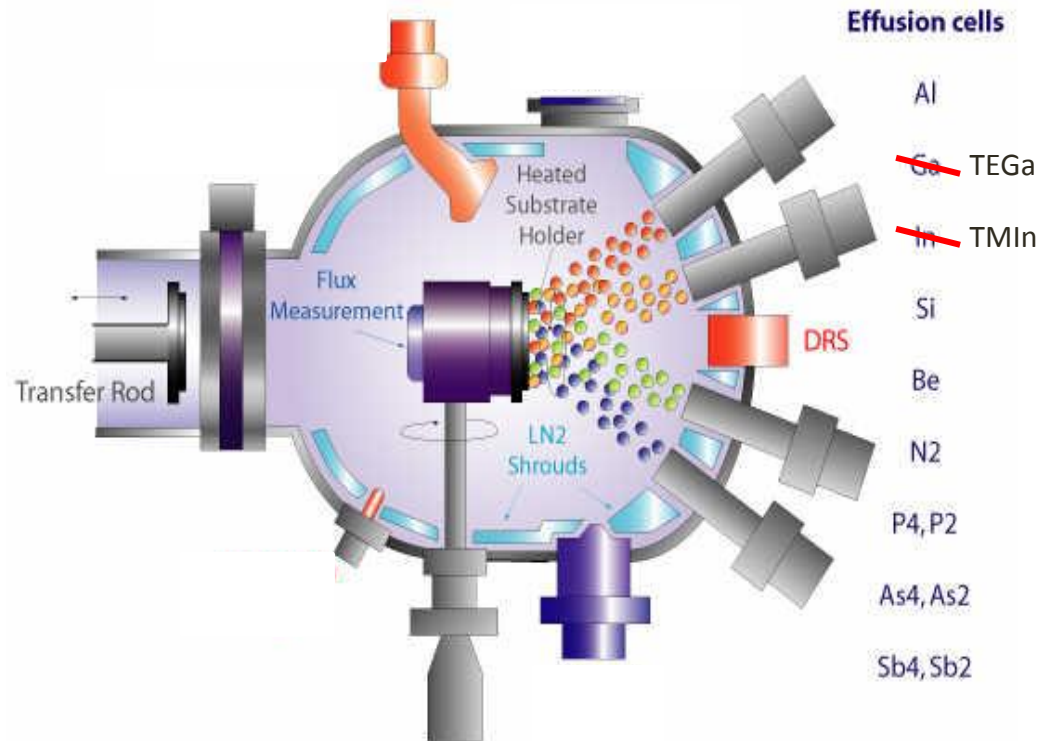
$\text{InAs}_x\text{P}_{1-x}$ layer

InP substrate

Growth by Chemical Beam Epitaxy (CBE)

- Liquid or gas sources
- Alloy group V elements
- Switch sources without compromising vacuum
- Faster growth rate than molecular beam epitaxy

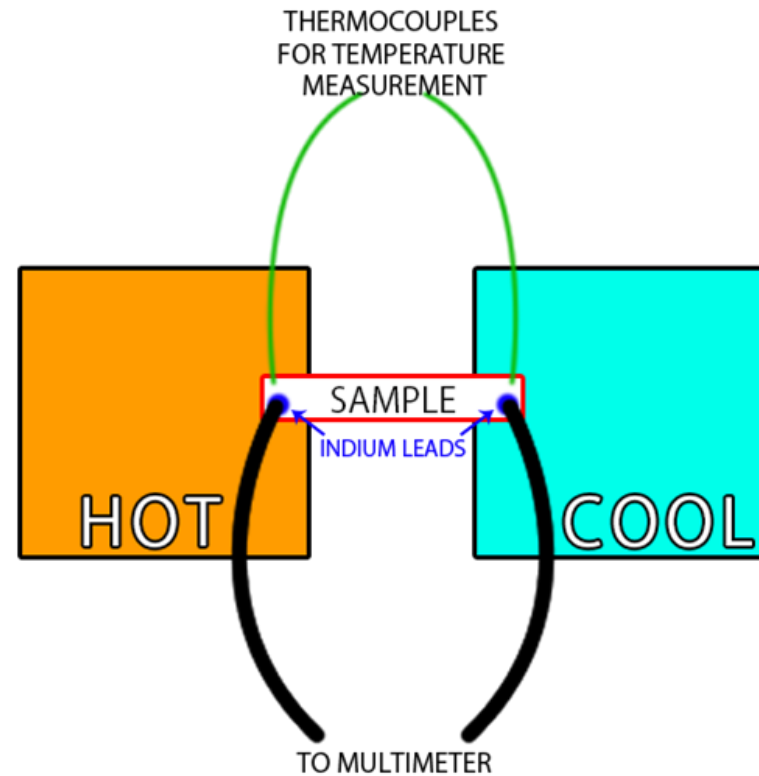
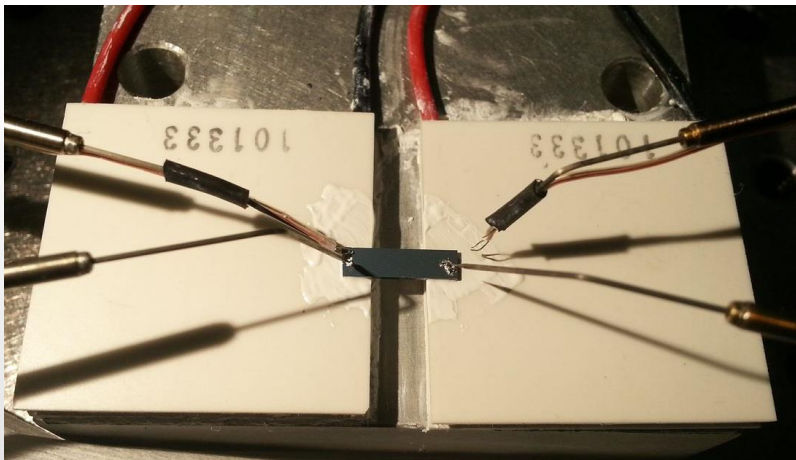
Arsine, phosphine, and trimethyl indium gases are beamed at InP substrate to grow the material



“Thermopower” – The Seebeck Coefficient

$$ZT = \frac{\alpha^2 \sigma}{\kappa} T$$

$$\alpha = \frac{\Delta V}{\Delta T}$$



The Hall Effect and Electrical Conductivity

$$ZT = \frac{\alpha^2 \sigma}{\kappa} T$$

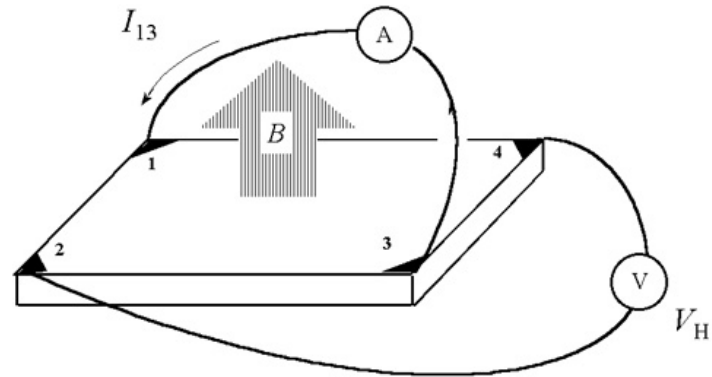
$\sigma =$ carrier density

×

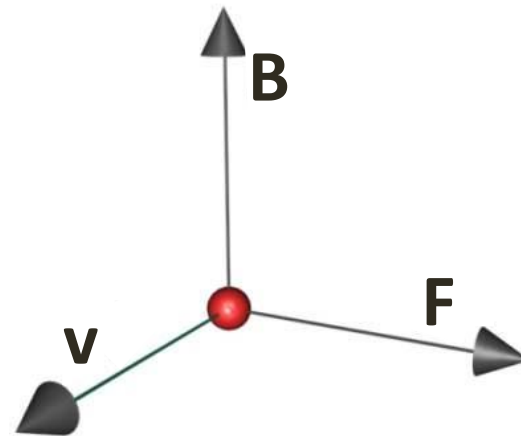
carrier mobility

×

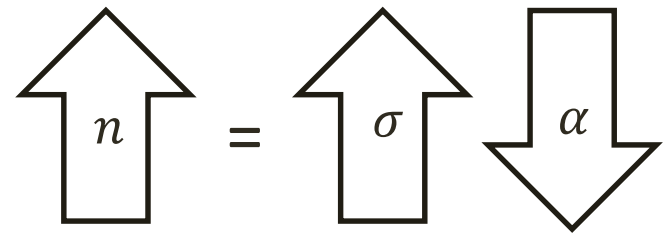
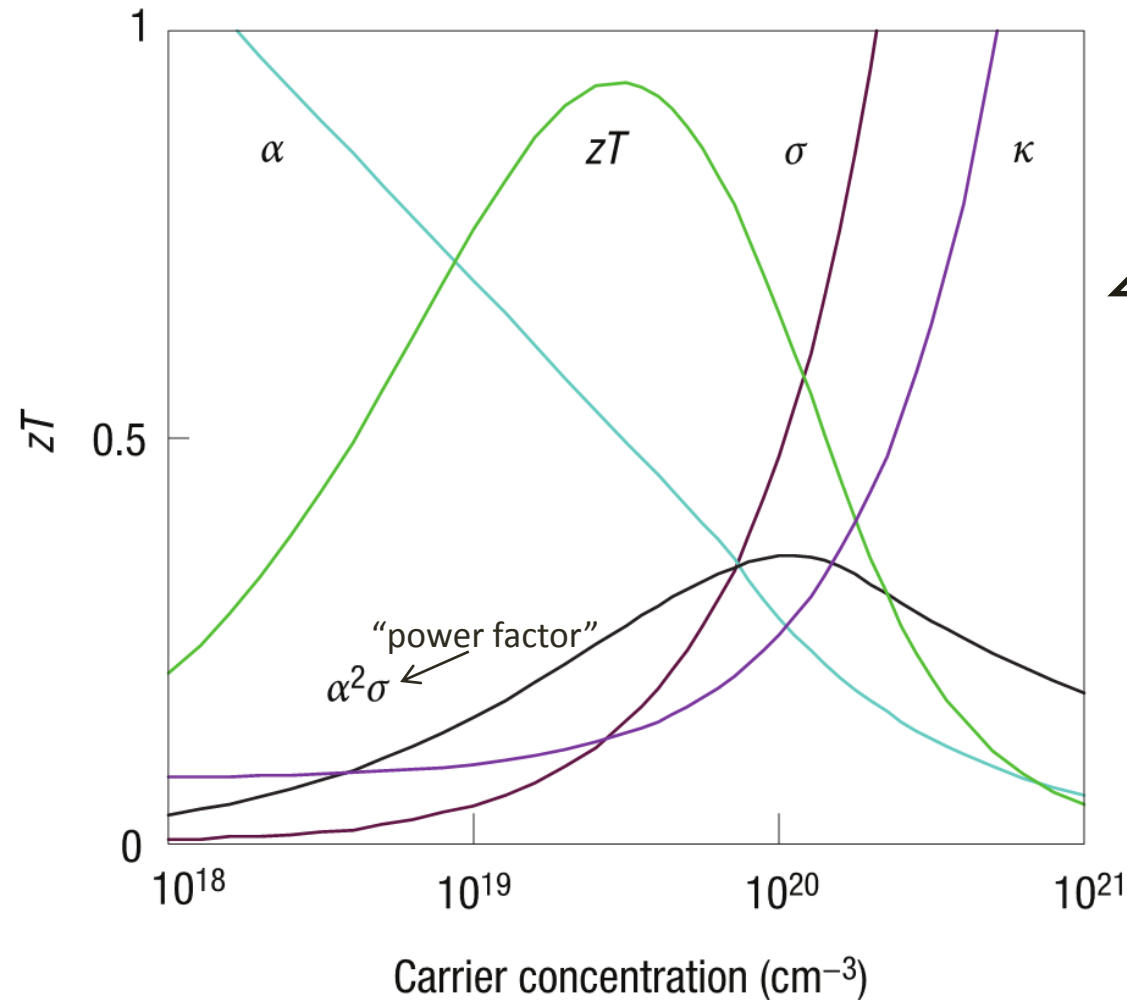
elementary charge



Original Image: <http://tau.nanophys.kth.se/cmp/hall/node5.htm>



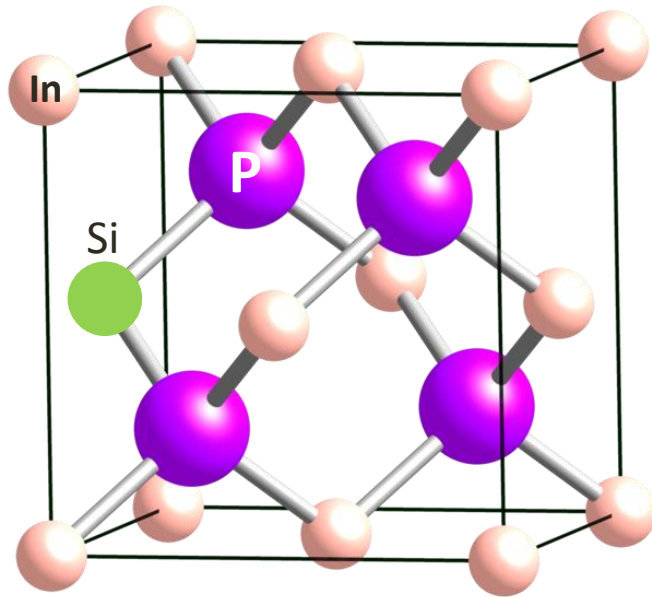
Balancing the Components of ZT



$$ZT = \frac{\alpha^2 \sigma}{\kappa} T$$

The equation shows the figure of merit ZT as a function of temperature T . Red arrows indicate that α decreases (downward arrow) and σ increases (upward arrow) with carrier concentration.

Conventionally (Si) doped InP

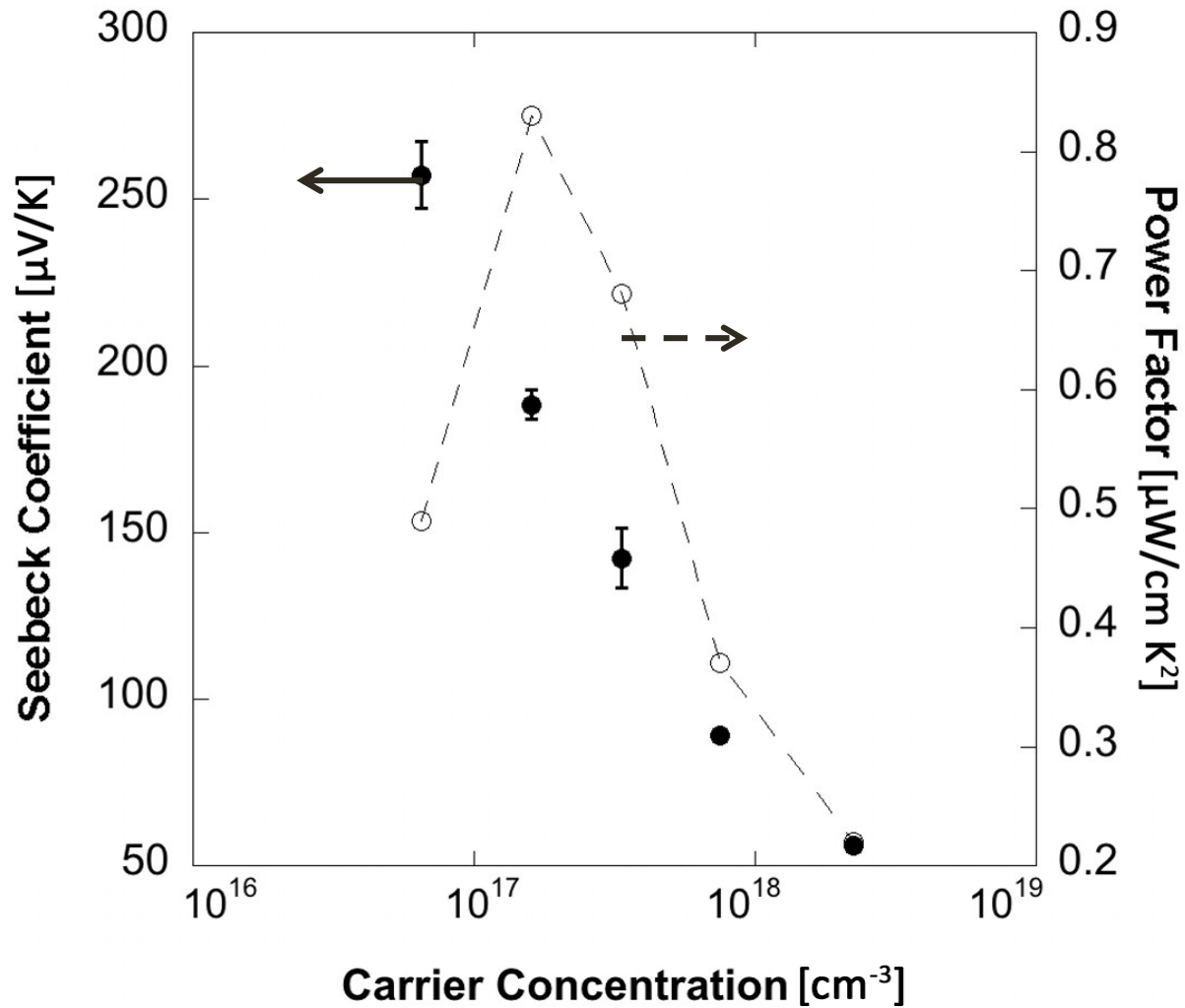


Original image: Public Domain

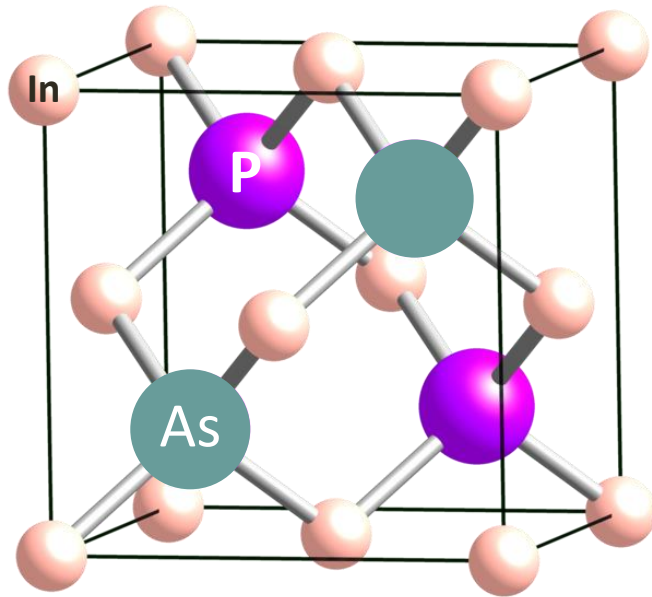
III	IV	V	VI
boron 5 B 10.811	carbon 6 C 12.011	nitrogen 7 N 14.007	oxygen 8 O 15.999
aluminium 13 Al 26.982	silicon 14 Si 28.086	phosphorus 15 P 30.974	sulfur 16 S 32.065
gallium 31 Ga 69.723	germanium 32 Ge 72.61	arsenic 33 As 74.922	selenium 34 Se 78.96
indium 49 In 114.82	tin 50 Sn 118.71	antimony 51 Sb 121.76	tellurium 52 Te 127.60
thallium 81 Tl 204.38	lead 82 Pb 207.2	bismuth 83 Bi 208.98	polonium 84 Po [209]

Original image: <http://www.bpc.edu/>

Conventionally (Si) doped InP



Unintentionally (UID) doped InAsP

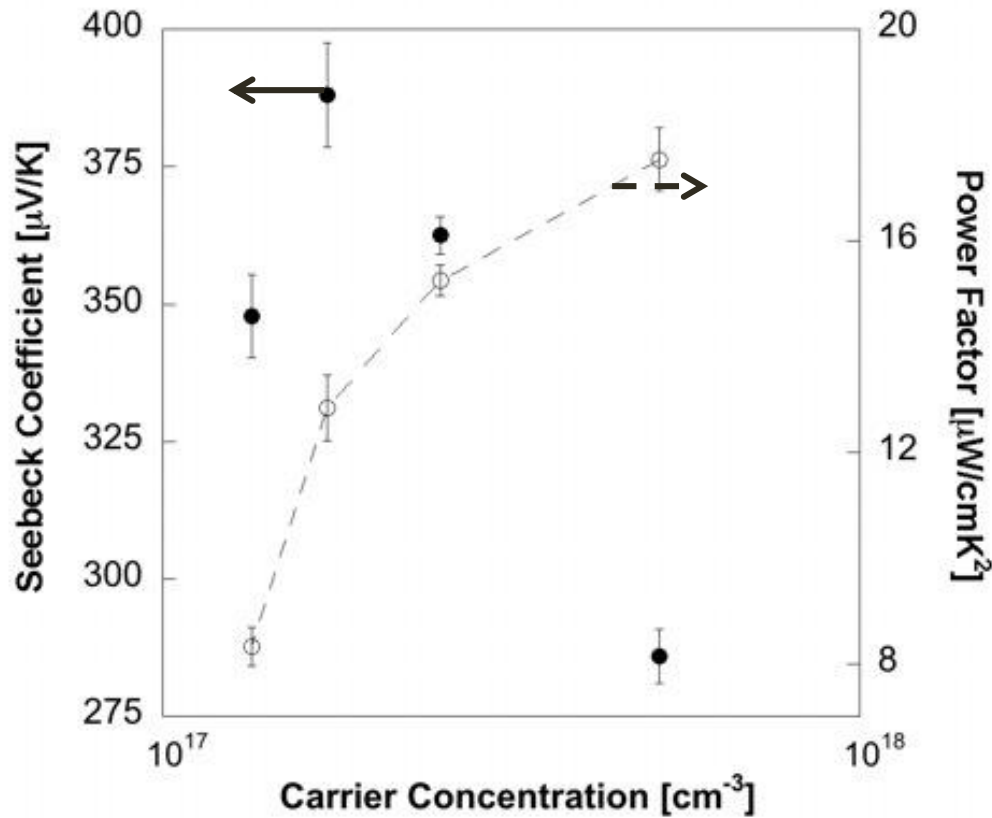


Original image: Public Domain

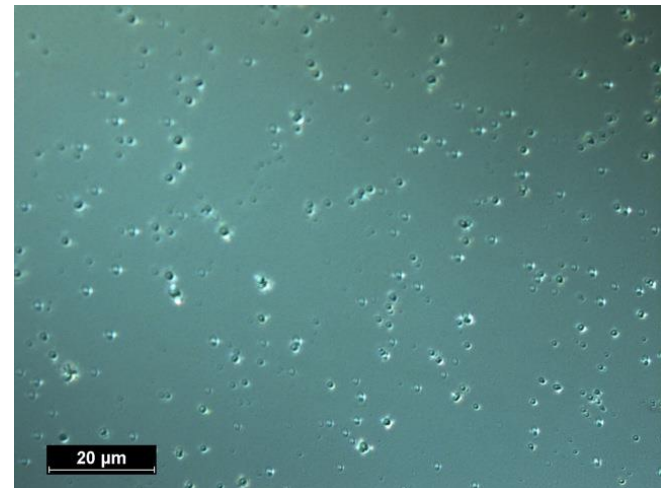
III	IV	V	VI
boron 5 B 10.811	carbon 6 C 12.011	nitrogen 7 N 14.007	oxygen 8 O 15.999
aluminium 13 Al 26.982	silicon 14 Si 28.086	phosphorus 15 P 30.974	sulfur 16 S 32.065
gallium 31 Ga 69.723	germanium 32 Ge 72.61	arsenic 33 As 74.922	selenium 34 Se 78.96
indium 49 In 114.82	tin 50 Sn 118.71	antimony 51 Sb 121.76	tellurium 52 Te 127.60
thallium 81 Tl 204.38	lead 82 Pb 207.2	bismuth 83 Bi 208.98	polonium 84 Po [209]

Original image: <http://www.bpc.edu/>

Unintentionally (UID) doped InAsP



III/V ratio too high \rightarrow Indium droplets

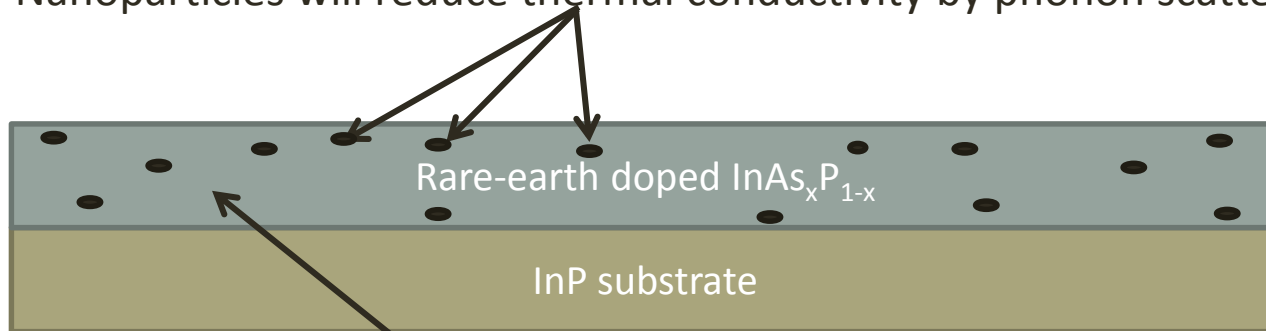


Future Goals

InP ----- InAs_xP_{1-x} ----- InAs

Si	✓		
UID		✓	
Er			

Nanoparticles will reduce thermal conductivity by phonon scattering



Rare earth dopants provide charge carriers

- Explore other rare earth elements (e.g. lanthanum) to compare with erbium- and conventionally-doped samples

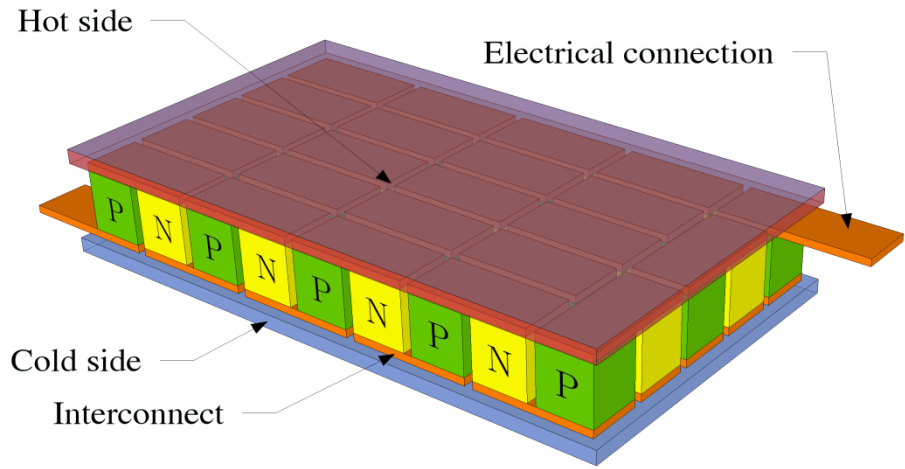
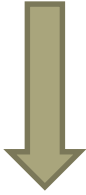
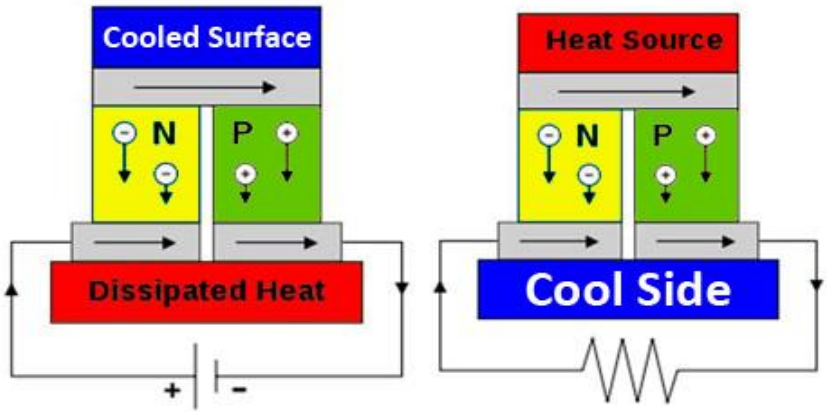
Acknowledgements



Ryan Need

Christopher Palmstrøm

The Thermoelectric Effect



Thermoelectric Efficiency

